

ABSTRACT

A semiconductor device including a substrate; an insulating layer disposed on the substrate, and including an outer boundary; a passivation layer disposed on the insulating layer, and including an inner boundary that
5 is located inward of the outer boundary; a dummy pattern layer having a lower surface that forms the same plane with the lower surface of the passivation layer, overlapping at least a part of a region disposed between the outer and inner boundaries, and having a side surface that is located inward of the inner boundary; and a redistribution pattern layer disposed
10 on the dummy pattern layer.

FIG. 3